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|  | <h2>SI1427EDH-T1-GE3</h2> |
| | <p>Hersteller-Teilenummer: SI1427EDH-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 2A SOT-363</p> <p>Datenblätter:  SI1427EDH-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 32980 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

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|--|---|
| Teilenummer | SI1427EDH-T1-GE3 |
| Hersteller | Vishay / Siliconix |
| Beschreibung | MOSFET P-CH 20V 2A SOT-363 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 32980 pcs Stock |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | 6-TSSOP, SC-88, SOT-363 |
| Supplier Device-Gehäuse | SC-70-6 (SOT-363) |
| Verlustleistung (max) | 1.56W (Ta), 2.8W (Tc) |
| Typ FET | P-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 20V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 2A (Tc) |
| Rds On (Max) @ Id, Vgs | 64 mOhm @ 3A, 4.5V |
| VGS (th) (Max) @ Id | 1V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 21nC @ 8V |
| Eingabekapazität (Ciss) (Max) @ Vds | - |
| Antriebsspannung (Max Rds On, Min Rds On) | 1.5V, 4.5V |
| Vgs (Max) | ±8V |
| Verpackung | Tape & Reel (TR) |

























SI1427EDH-T1-GE3 ist neu im Original, Suche SI1427EDH-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1427EDH-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI1427EDH-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

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|  <p>SI1427EDH-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 2A SOT-363</p> |  <p>SI1428EDH-T1-GE3 VISHAY VISHAY SC70-6</p> |  <p>SI1431DH-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 1.7A SOT363</p> |  <p>SI1428EDH-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CHANNEL 30V 4A SC70-6</p> |
|  <p>SI1426DH-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 2.8A SC70-6</p> |  <p>SI1426DH-T1-E3 Vishay / Siliconix MOSFET N-CH 30V 2.8A SC70-6</p> |  <p>SI1431DH-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 1.7A SOT363</p> |  <p>SI1426DH-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 2.8A SC70-6</p> |

heiße Teile

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|  SI1413EDH-T1 |  SI1413EDH-T1-E3 |  SI1413EDH-T1-E3 |  SI1413EDH-T1-GE3 |  SI1413EDH-T1-GE3 |
|  SI1414DH-T1-GE3 |  SI1414DH-T1-GE3 |  SI1416EDH-T1-GE3 |  SI1416EDH-T1-GE3 |  SI1417DH-T1-E3 |
|  SI1417DH-T1-GE3 |  SI1417EDH-T1 |  SI1417EDH-T1-E3 |  SI1417EDH-T1-E3 |  SI1417EDH-T1-GE3 |
|  SI1417EDH-T1-GE3 |  SI1422DH-T1-GE3 |  SI1422DH-T1-GE3 |  SI1424EDH-T1-GE3 |  SI1424EDH-T1-GE3 |
|  SI1426DH-T1-E3 |  SI1426DH-T1-E3 |  SI1426DH-T1-GE3 |  SI1426DH-T1-GE3 |  SI1427EDH-T1-GE3 |
|  SI1428EDH-T1-GE3 |  SI1428EDH-T1-GE3 |  SI1433DH-T1 |  SI1433DH-T1-E3 |  SI1433DH-T1-E3 |
|  SI1433DH-T1-GE3 |  SI1433DH-T1-GE3 |  SI1441EDH-T1-GE3 |  SI1441EDH-T1-GE3 |  SI1442DH-T1-GE3 |
|  SI1442DH-T1-GE3 |  SI1443EDH-T1-GE3 |  SI1443EDH-T1-GE3 |  SI1467DH-T1-GE3 |  SI1467DH-T1-GE3 |
|  SI1469DH-T1-GE3 |  SI1469DH-T1-GE3 |  SI1470DH-M6TR |  SI1470DH-T1-GE3 |  SI1470DH-T1-GE3 |
|  SI1471DH-T1 |  SI1471DH-T1-E3 |  SI1471DH-T1-E3 |  SI1471DH-T1-GE3 |  SI1471DH-T1-GE3 |

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